## Medium Power Transistor multicomp







### **Pin Configuration**

- 1. Emitter
- 2. Base
- 3. Collector

### Features:

- · High performance, low frequency devices typically with current ratings 2A. Up to 1W power dissipation
- PNP Epitaxial Planar Silicon Transistors

## **Absolute Maximum Ratings:**

(TA = 25°C unless otherwise specified)

Characteristic	Symbol	Value	Unit
Collector-Emitter Voltage lb=0	V <sub>CEO (sus)</sub>	60	
Collector-Emitter Voltage $R_{BE} = 100\Omega$	V <sub>CER</sub>	75	V
Emitter-Base Voltage	V <sub>EBO</sub>	5	
Collector Current	lc	1	
Collector Peak Current	I <sub>CM</sub>	2	A
Base Current	I <sub>B</sub>	0.5	
Power Dissipation at T <sub>A</sub> = 25°C at T <sub>C</sub> = 25°C	P <sub>tot</sub>	1 10	W
Operating Storage Temperature Range	$T_{J}, T_{stg}$	-65 to +200	°C

### **Thermal Resistance**

Junction to Ambient	$R_{th(j-a)}$	17.5	°C/M
Junction to Case	R <sub>th(j-c)</sub>	17.5	°C/W



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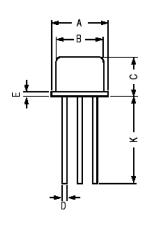
### **Electrical Characteristics:**

(T<sub>o</sub> = +25°C unless otherwise specified)

Parameter	Symbol	Test Condition	Min.	Max.	Unit
Collector Cut off Current D = 1000	I <sub>CBO</sub>	$V_{CB} = 40V, I_{E} = 0$		100	nA
Collector-Cut off Current $R_{BE} = 100\Omega$	I <sub>CER</sub>	V <sub>CE</sub> = 60V	_	10	μA
Collector-Emitter Voltage	V <sub>CEO</sub> *	$I_{\rm C} = 10  \text{mA}, I_{\rm B} = 0$	60		V
Emitter-Base Voltage	$V_{\scriptscriptstyle{EBO}}$	$I_{E} = 100 \mu A, I_{C} = 0$	5	5	
DC Current Gain	h <sub>FE</sub> *	I <sub>C</sub> = 500mA, V <sub>CE</sub> = 4V	40	250	-
Collector Emitter Saturation Voltage	V <sub>CE(Sat)</sub> *	I <sub>C</sub> = 1,000mA, I <sub>B</sub> = 100mA		1	V
Base Emitter Saturation Voltage	V <sub>BE(sat)</sub> *	I <sub>C</sub> = 1A, I <sub>B</sub> = 100mA	_	1.5	V
Transition Frequency	f <sub>t</sub>	$I_{\rm C}$ = 50mA, $V_{\rm CE}$ = 4V, f = 1MHz	50	-	MHz

<sup>\*</sup>Pulse: Pulse Duration = 300µs, Duty Cycle = 1%

### **TO-39 Metal Can Package**

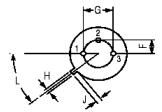


Α	8.5	9.39
В	7.74	8.5
С	6.09	6.6
D	0.4	0.53
Е	-	0.88
F	2.41	2.66
G	4.82	5.33
Н	0.71	0.86
J	0.73	1.02
K	12.7	-
Ĺ	42°	48°

Min.

Max.

**Dimensions: Millimetres** 



### **Pin Configuration**

- 1. Emitter
- 2. Base

Dim.

3. Collector

### **Part Number Table**

Description	Part Number	
Transistor, PNP, TO-39	BC461	

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